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Fax Cover Sheet

DATE:	July 2, 2003	PAGES:	<u>10 (ten) w/cover</u>
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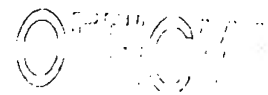
Message

DOCKET GS 150

Please see attached: Response After Final Rejection

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Response after Final Rejection
Expedited Handling Requested - GAU 2826

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Patent
10/010,484

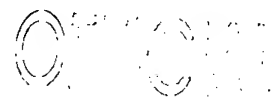
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Hshieh et al.
Serial No.: 10/010,484
Filed: November 20, 2001
Title: Trench MOSFET Device with Polycrystalline Silicon Source Contact Structure
Art Unit: 2826
Examiner: Tan N. Tran
Docket No.: GS 150

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Commissioner for Patents
PO Box 1450
Alexandria, VA 22313-1450



RESPONSE AFTER FINAL REJECTION

Sir:

In response to the second final Office Action dated July 23, 2003 (Paper No. 12), kindly consider the following remarks. In addition, any deficiencies may be charged to deposit account No. 50-1047.